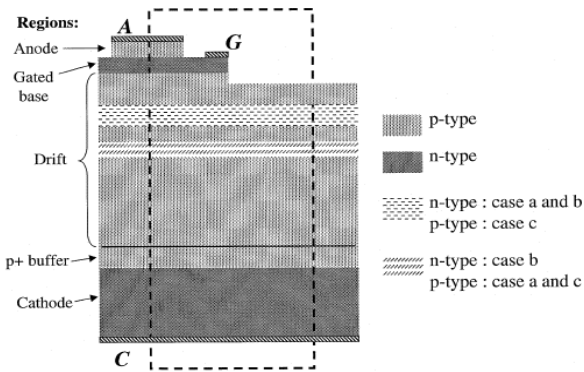


Technology Brief

SiC GTO Thyristors

US Patents

6,900,477 __ 6,734,462
6,703,642 __ 6,472,686



OVERVIEW

This technology includes new operational techniques, growth requirements, and structures to improve the power handling capability of SiC gate turn-off thyristors.

POTENTIAL USES

Potential uses include the design and production of high power, high temperature devices for use as semiconductor electronic switches.

ADVANTAGES

- Improved power handling
- Improved turn-off gains
- Faster switching
- Higher voltage blocking
- Higher temperature operation

DEVELOPMENT STATUS/OPPORTUNITY

The technology was developed at a US Army Research Lab. Structures have been designed and evaluated through simulation. Four US patents have been issued relating to this technology. Partners are sought for licensing, development & commercialization.



Contact for commercialization opportunities
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